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Kind regards,

Team Nexperia

DATA SHEET

PEMH7; PUMH7

**NPN/NPN resistor-equipped
transistors; R1 = 4.7 k Ω , R2 = open**

Product data sheet
Supersedes data of 2001 Oct 22

2003 Oct 02

**NPN/NPN resistor-equipped transistors;
R1 = 4.7 kΩ, R2 = open**

PEMH7; PUMH7

FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- Low current peripheral driver
- Replacement of general purpose transistors in digital applications
- Control of IC inputs.

QUICK REFERENCE DATA

| SYMBOL | PARAMETER | TYP. | MAX. | UNIT |
|------------------|---------------------------|------|------|------|
| V _{CEO} | collector-emitter voltage | – | 50 | V |
| I _O | output current (DC) | – | 100 | mA |
| TR1 | NPN | – | – | – |
| TR2 | NPN | – | – | – |
| R1 | bias resistor | 4.7 | – | kΩ |
| R2 | bias resistor | open | – | – |

DESCRIPTION

NPN/NPN resistor-equipped transistors (see “Simplified outline, symbol and pinning” for package details).

PRODUCT OVERVIEW

| TYPE NUMBER | PACKAGE | | MARKING CODE ⁽¹⁾ | NPN/PNP COMPLEMENT | PNP/PNP COMPLEMENT |
|-------------|---------|-------|-----------------------------|--------------------|--------------------|
| | PHILIPS | EIAJ | | | |
| PEMH7 | SOT666 | – | H3 | PEMD6 | PEMB3 |
| PUMH7 | SOT363 | SC-88 | H*7 | PUMD6 | PUMB3 |

Note

- * = p: Made in Hong Kong.
* = t: Made in Malaysia.

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

| TYPE NUMBER | SIMPLIFIED OUTLINE AND SYMBOL | PINNING | |
|----------------|---|---------|---------------|
| | | PIN | DESCRIPTION |
| PEMH7 PUMH7 | <p>Top view MAM453</p> | 1 | emitter TR1 |
| | | 2 | base TR1 |
| | | 3 | collector TR2 |
| | | 4 | emitter TR2 |
| | | 5 | base TR2 |
| | | 6 | collector TR1 |

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ORDERING INFORMATION

| TYPE NUMBER | PACKAGE | | |
|-------------|---------|--|---------|
| | NAME | DESCRIPTION | VERSION |
| PEMH7 | – | Plastic surface mounted package; 6 leads | SOT666 |
| PUMH7 | – | Plastic surface mounted package; 6 leads | SOT363 |

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-----------------------|-------------------------------|--------------------------|------|------|------|
| Per transistor | | | | | |
| V _{CBO} | collector-base voltage | open emitter | – | 50 | V |
| V _{CEO} | collector-emitter voltage | open base | – | 50 | V |
| V _{EBO} | emitter-base voltage | open collector | – | 5 | V |
| I _O | output current (DC) | | – | 100 | mA |
| I _{CM} | peak collector current | | – | 100 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | | | |
| | SOT363 | note 1 | – | 200 | mW |
| | SOT666 | notes 1 and 2 | – | 200 | mW |
| T _{stg} | storage temperature | | –65 | +150 | °C |
| T _j | junction temperature | | – | 150 | °C |
| T _{amb} | operating ambient temperature | | –65 | +150 | °C |
| Per device | | | | | |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | | | |
| | SOT363 | note 1 | – | 300 | mW |
| | SOT666 | notes 1 and 2 | – | 300 | mW |

Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
2. Reflow soldering is the only recommended soldering method.

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THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|-----------------------|---|--------------------------|-------|------|
| Per transistor | | | | |
| R _{th j-a} | thermal resistance from junction to ambient | T _{amb} ≤ 25 °C | | |
| | SOT363 | note 1 | 625 | K/W |
| | SOT666 | notes 1 and 2 | 625 | K/W |
| Per device | | | | |
| R _{th j-a} | thermal resistance from junction to ambient | T _{amb} ≤ 25 °C | | |
| | SOT363 | note 1 | 416 | K/W |
| | SOT666 | notes 1 and 2 | 416 | K/W |

Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
2. Reflow soldering is the only recommended soldering method.

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------------------|--------------------------------------|--|------|------|------|------------|
| Per transistor | | | | | | |
| I _{CBO} | collector-base cut-off current | V _{CB} = 50 V; I _E = 0 | – | – | 100 | nA |
| I _{CEO} | collector-emitter cut-off current | V _{CE} = 30 V; I _B = 0 | – | – | 1 | μ A |
| | | V _{CE} = 30 V; I _B = 0; T _j = 150 °C | – | – | 50 | μ A |
| I _{EBO} | emitter-base cut-off current | V _{EB} = 5 V; I _C = 0 | – | – | 100 | nA |
| h _{FE} | DC current gain | V _{CE} = 5 V; I _C = 1 mA | 200 | 330 | – | |
| V _{CEsat} | collector-emitter saturation voltage | I _C = 5 mA; I _B = 0.25 mA | – | – | 100 | mV |
| R1 | input resistor | | 3.3 | 4.7 | 6.1 | k Ω |
| C _c | collector capacitance | V _{CB} = 10 V; I _E = i _e = 0; f = 1 MHz | – | – | 2.5 | pF |

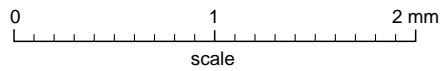
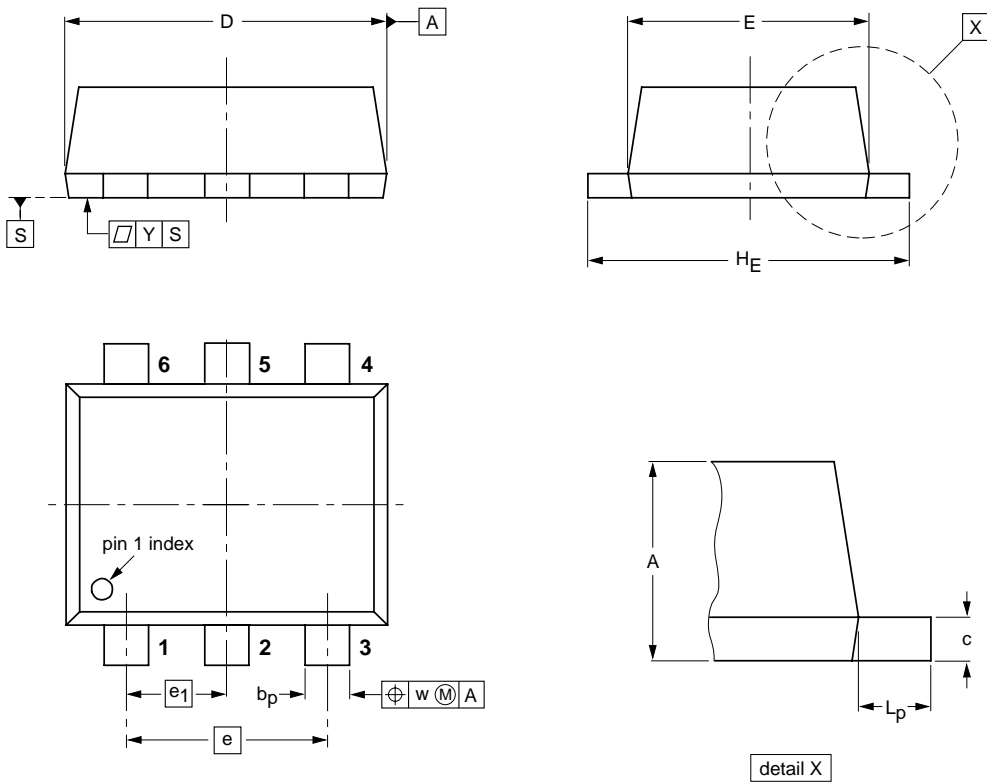
NPN/NPN resistor-equipped transistors;
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



DIMENSIONS (mm are the original dimensions)

| UNIT | A | b_p | c | D | E | e | e_1 | H_E | L_p | w | y |
|------|------------|--------------|--------------|------------|------------|-----|-------|------------|------------|-----|-----|
| mm | 0.6 0.5 | 0.27 0.17 | 0.18 0.08 | 1.7 1.5 | 1.3 1.1 | 1.0 | 0.5 | 1.7 1.5 | 0.3 0.1 | 0.1 | 0.1 |

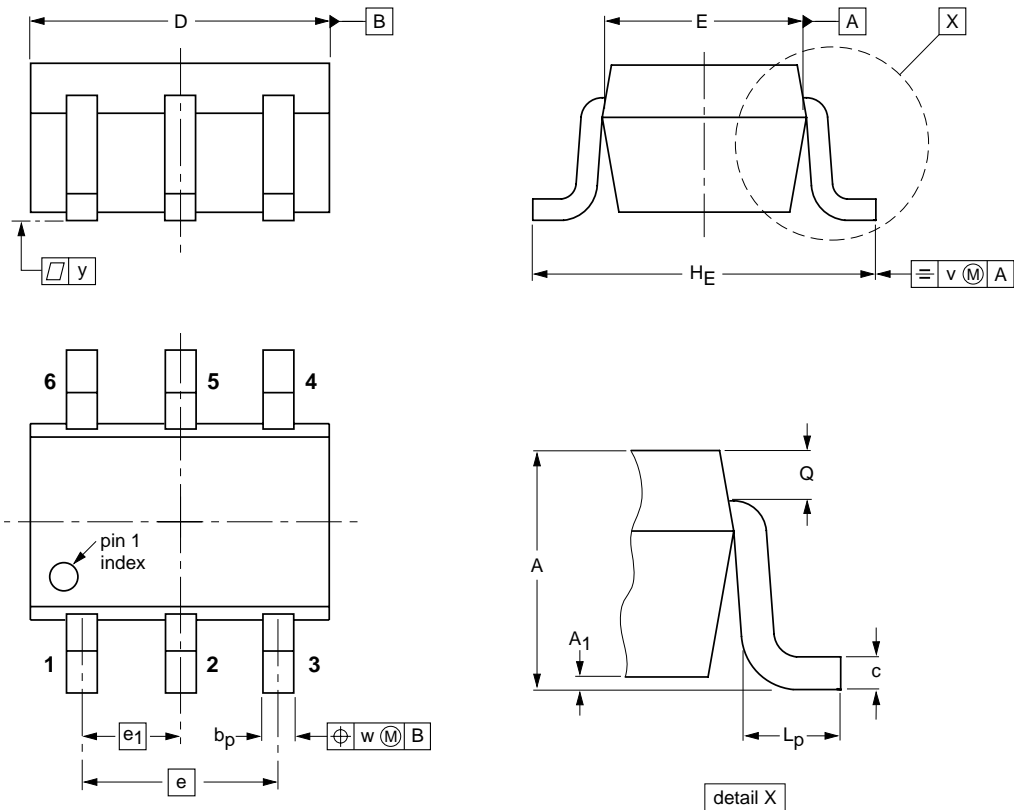
| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|-----------------|------------|-------|------|--|---------------------|----------------------|
| | IEC | JEDEC | EIAJ | | | |
| SOT666 | | | | | | 01-01-04 01-08-27 |

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SOT363



DIMENSIONS (mm are the original dimensions)

| UNIT | A | A1 max | bp | c | D | E | e | e1 | HE | Lp | Q | v | w | y |
|------|------------|-----------|--------------|--------------|------------|--------------|-----|------|------------|--------------|--------------|-----|-----|-----|
| mm | 1.1 0.8 | 0.1 | 0.30 0.20 | 0.25 0.10 | 2.2 1.8 | 1.35 1.15 | 1.3 | 0.65 | 2.2 2.0 | 0.45 0.15 | 0.25 0.15 | 0.2 | 0.2 | 0.1 |

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|--------------------|------------|-------|-------|--|------------------------|------------|
| | IEC | JEDEC | EIAJ | | | |
| SOT363 | | | SC-88 | | | 97-02-28 |

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DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|--------------------------------|-------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

Notes

1. Please consult the most recently issued document before initiating or completing a design.
2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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